

Low $V_{CE(sat)}$ Transistor, PNP, 12 V, 1 A, SOT-563 Package NSS12100XV6T1G

12 VOLTS, 1.0 AMPS
PNP LOW $V_{CE(sat)}$ TRANSISTOR
EQUIVALENT $R_{DS(on)}$ 300 m Ω

onsemi's e²PowerEdge family of low $V_{CE(sat)}$ transistors are miniature surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical application are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e²PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

Features

- High Current Capability (1 A)
- High Power Handling (Up to 650 mW)
- Low $V_{CE(s)}$ (150 mV Typical @ 500 mA)
- Small Size
- This is a Pb-Free Device

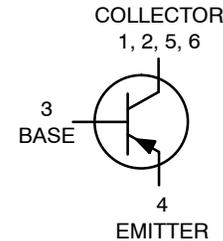
Benefits

- High Specific Current and Power Capability Reduces Required PCB Area
- Reduced Parasitic Losses Increases Battery Life

MAXIMUM RATINGS (T_A = 25 °C)

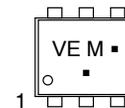
Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V_{CEO}	-12	Vdc
Collector-Base Voltage	V_{CBO}	-12	Vdc
Emitter-Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current – Continuous – Peak	I_C I_{CM}	-1.0 -2.0	Adc
Electrostatic Discharge	ESD	HBM Class 3 MM Class C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



1
SOT-563
CASE 463A
STYLE 4

DEVICE MARKING



VE = Specific Device Code
M = Month Code
▪ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NSS12100XV6T1G	SOT-563 (Pb-Free)	4000 / Tape & Reel

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, [BRD8011/D](#).

NSS12100XV6T1G

THEMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation $T_A = 25\text{ }^\circ\text{C}$ Derate above $25\text{ }^\circ\text{C}$	P_D (Note 1)	500	mW
		4.0	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$ (Note 1)	250	$^\circ\text{C/W}$
Total Device Dissipation $T_A = 25\text{ }^\circ\text{C}$ Derate above $25\text{ }^\circ\text{C}$	P_D (Note 2)	650	mW
		5.2	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$ (Note 2)	192	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Lead 6	$R_{\theta JL}$	105	$^\circ\text{C/W}$
Total Device Dissipation (Single Pulse < 10 sec.)	P_D Single	1.0	W
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage, ($I_C = -10\text{ mAdc}, I_B = 0$)	$V_{(BR)CEO}$	-12	-	-	Vdc
Collector-Base Breakdown Voltage, ($I_C = -0.1\text{ mAdc}, I_E = 0$)	$V_{(BR)CBO}$	-12	-	-	Vdc
Emitter-Base Breakdown Voltage, ($I_E = -0.1\text{ mAdc}, I_C = 0$)	$V_{(BR)EBO}$	-5.0	-	-	Vdc
Collector Cutoff Current, ($V_{CB} = -12\text{ Vdc}, I_E = 0$)	I_{CBO}	-	-0.02	-0.1	μAdc
Emitter Cutoff Current, ($V_{CES} = -5.0\text{ Vdc}, I_E = 0$)	I_{EBO}	-	-0.03	-0.1	μAdc

ON CHARACTERISTICS

DC Current Gain (Note 3) ($I_C = -10\text{ mA}, V_{CE} = -2.0\text{ V}$) ($I_C = -500\text{ mA}, V_{CE} = -2.0\text{ V}$) ($I_C = -1.0\text{ A}, V_{CE} = -2.0\text{ V}$)	h_{FE}	200 100 90	- - -	- - -	
Collector-Emitter Saturation Voltage (Note 3) ($I_C = -0.05\text{ A}, I_B = -0.005\text{ A}$) (Note 4) ($I_C = -0.1\text{ A}, I_B = -0.002\text{ A}$) ($I_C = -0.1\text{ A}, I_B = -0.010\text{ A}$) ($I_C = -0.5\text{ A}, I_B = -0.050\text{ A}$) ($I_C = -1.0\text{ A}, I_B = -0.100\text{ A}$)	$V_{CE(sat)}$	- - - - -	-0.030 -0.080 -0.050 -0.200 -0.400	-0.040 -0.100 -0.060 -0.225 -0.440	V
Base-Emitter Saturation Voltage (Note 3) ($I_C = -1.0\text{ A}, I_B = -0.01\text{ A}$)	$V_{BE(sat)}$	-	0.95	-1.15	V
Base-Emitter Turn-on Voltage (Note 3) ($I_C = -2.0\text{ A}, V_{CE} = -3.0\text{ V}$)	$V_{BE(on)}$	-	-1.05	-1.15	V
Input Capacitance ($V_{EB} = -0.5\text{ V}, f = 1.0\text{ MHz}$)	C_{ibo}	-	-	50	pF
Output Capacitance ($V_{CB} = -3.0\text{ V}, f = 1.0\text{ MHz}$)	C_{obo}	-	-	20	pF

1. FR-4 @ 100 mm², 1 oz copper traces.
2. FR-4 @ 500 mm², 1 oz copper traces.
3. Pulsed Condition: Pulse Width = 300 μsec , Duty Cycle $\leq 2\%$.
4. Guaranteed by design but not tested.

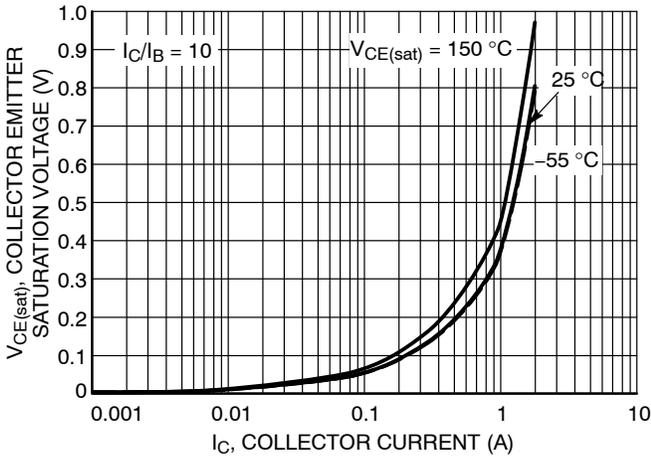


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

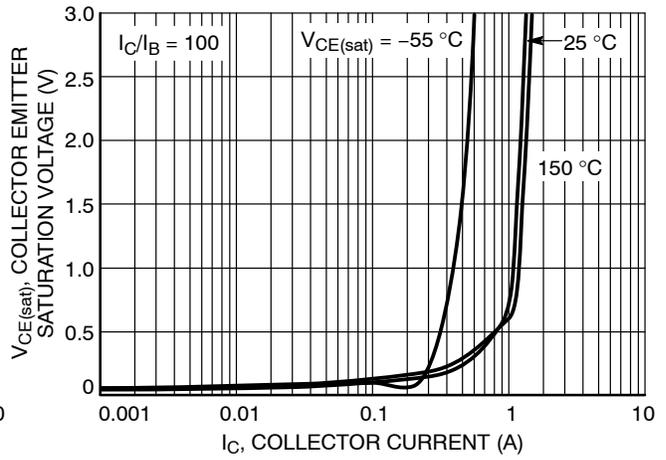


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

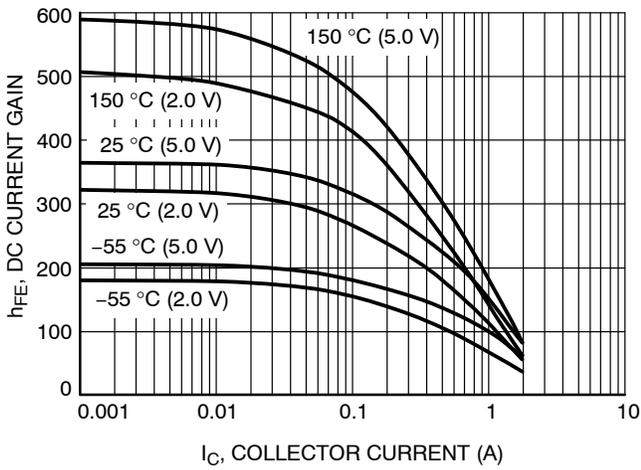


Figure 3. DC Current Gain vs. Collector Current

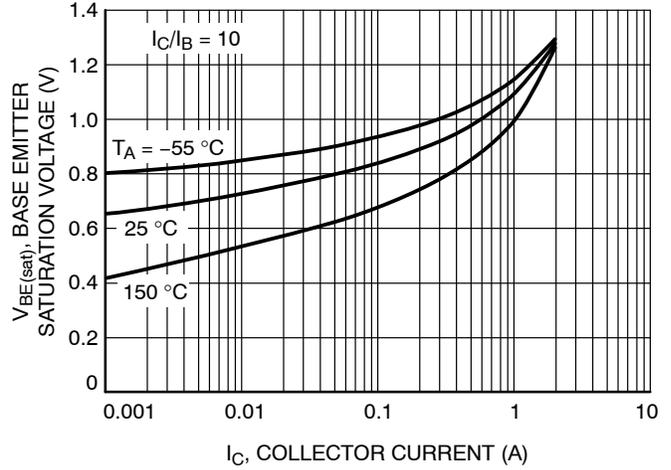


Figure 4. Base Emitter Saturation Voltage vs. Collector Current

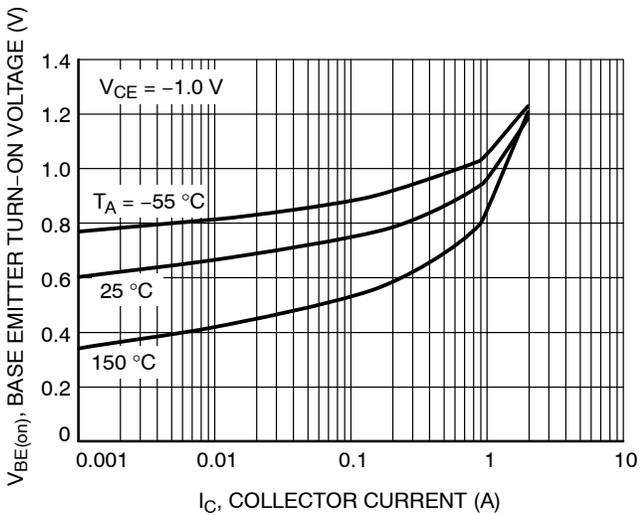


Figure 5. Base Emitter Turn-On Voltage vs. Collector Current

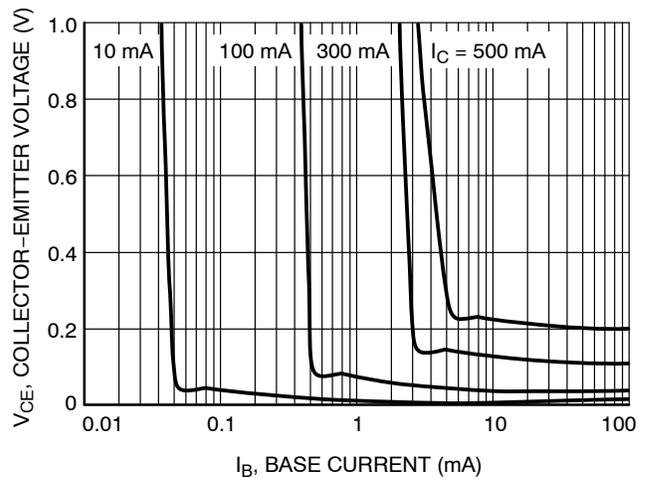


Figure 6. Saturation Region

NSS12100XV6T1G

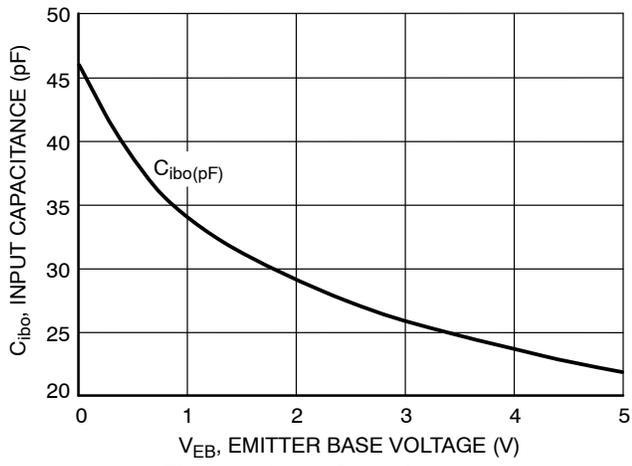


Figure 7. Input Capacitance

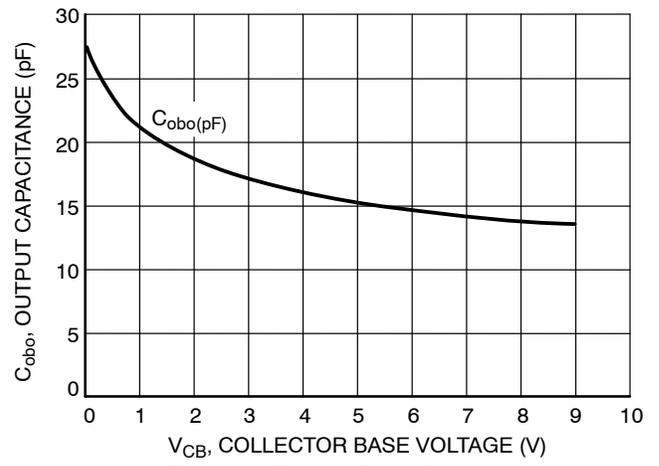


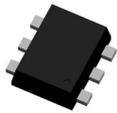
Figure 8. Output Capacitance

NSS12100XV6T1G

REVISION HISTORY

Revision	Description of Changes	Date
1	Rebranded the Data Sheet to onsemi format.	10/17/2025

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

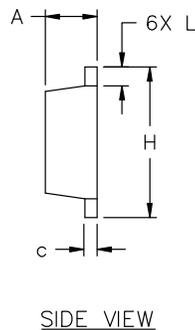
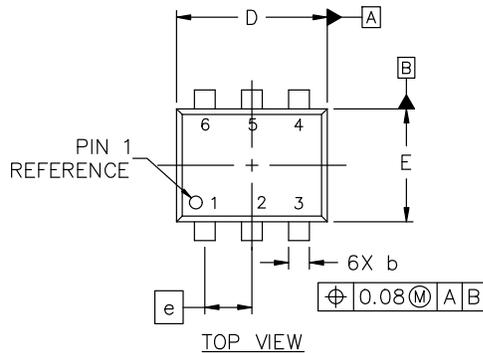


SOT-563-6 1.60x1.20x0.55, 0.50P
CASE 463A
ISSUE J

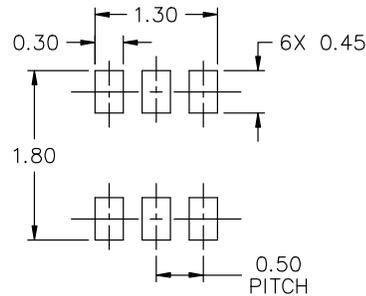
DATE 15 FEB 2024

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.50	0.55	0.60
b	0.17	0.22	0.27
c	0.08	0.13	0.18
D	1.50	1.60	1.70
E	1.10	1.20	1.30
e	0.50 BSC		
H	1.50	1.60	1.70
L	0.10	0.20	0.30



STYLE 1:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1

STYLE 2:
PIN 1. EMITTER 1
2. EMITTER 2
3. BASE 2
4. COLLECTOR 2
5. BASE 1
6. COLLECTOR 1

STYLE 3:
PIN 1. CATHODE 1
2. CATHODE 1
3. ANODE/ANODE 2
4. CATHODE 2
5. CATHODE 2
6. ANODE/ANODE 1

STYLE 4:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE
4. ANODE
5. CATHODE
6. CATHODE

STYLE 6:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE

STYLE 8:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 9:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

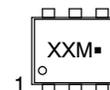
STYLE 10:
PIN 1. CATHODE 1
2. N/C
3. CATHODE 2
4. ANODE 2
5. N/C
6. ANODE 1

STYLE 11:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Month Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98AON11126D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOT-563-6 1.60x1.20x0.55, 0.50P	PAGE 1 OF 1

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales